

Photo FET Optocouplers H11F1M, H11F2M, H11F3M

General Description

The H11FXM series consists of a Gallium-Aluminum-Arsenide IRED emitting diode coupled to a symmetrical bilateral silicon photo-detector. The detector is electrically isolated from the input and performs like an ideal isolated FET designed for distortion-free control of low level AC and DC analog signals. The H11FXM series devices are mounted in dual in-line packages.

Features

- As a Remote Variable Resistor:
 - $\leq 100 \Omega$ to $\geq 300 M\Omega$
 - ≤15 pF Shunt Capacitance
 - ♦ \geq 100 GΩ I/O Isolation Resistance
- As an Analog Switch:
 - Extremely Low Offset Voltage
 - ullet 60 V_{pk-pk} Signal Capability
 - No Charge Injection or Latch-Up
 - UL Recognized (File #E90700)
- These are Pb-Free Devices

Application

- As a Remote Variable Resistor:
 - ◆ Isolated Variable Attenuator
 - Automatic Gain Control
 - ◆ Active Filter Fine Tuning/Band Switching
- As an Analog Switch:
 - Isolated Sample and Hold Circuit
 - Multiplexed, Optically Isolated A/D Conversion



PDIP6 8.51x6.35, 2.54P CASE 646BX

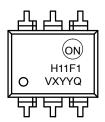


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MARKING DIAGRAM



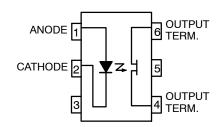
H11F1 = Specific Device Code

V = VDE Mark (Only appears on parts ordered with VDE option – See order entry table)

X = One-Digit Year Code, e.g., "7" YY = Two Digit Work Week Ranging from "01" to "53"

Q = Assembly Package Code

SCHEMATIC



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet

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SAFETY AND INSULATION RATINGS

(As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.)

Parameter	Characteristics	
Installation Classifications per DIN VDE 0110/1.89 Table 1	< 150 Vrms	I–IV
	< 300 Vrms	I–IV
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V _{PR}	Input to Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	$V_{ m peak}$
	Input to Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1594	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	850	V_{peak}
V _{IOTM}	Highest Allowable Over Voltage	6,000	V_{peak}
	External Creepage	≥7	mm
	External Clearance	≥7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥0.5	mm
T _S	Case Temperature (Note 1)	175	°C
I _{S,INPUT}	Input Current (Note 1)	350	mA
P _{S,OUTPUT}	Output Power (Note 1)	800	mW
R _{IO}	Insulation Resistance at Ts, V _{IO} = 500 V (Note 1)	>10 ⁹	Ω

^{1.} Safety limit values - maximum values allowed in the event of a failure.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C unless otherwise specified)

Symbol	Parameter	Value	Unit	
TOTAL DEV	ICE			
T _{STG}	Storage Temperature	-40 to +150	°C	
T _{OPR}	Operating Temperature		-40 to +100	°C
T _{SOL}	Lead Solder Temperature		260 for 10 seconds	°C
EMITTER				
l _F	Continuous Forward Current	60	mA	
V _R	Reverse Voltage	5	V	
I _F (pk)	Forward Current – Peak (10 µs Pulse, 1% Duty Cycle)	1	Α	
P_{D}	LED Power Dissipation Ambient 25°C Ambient		100	mW
	Derate Linearly from 25°C		1.33	mW/°C
DETECTOR				
P_{D}	Detector Power Dissipation at 25°C		300	mW
	Derate Linearly from 25°C	4.0	mW/°C	
BV ₄₋₆	Breakdown Voltage (Either Polarity) H11F1M, H11F2M		±30	V
		H11F3M	±15	V
I ₄₋₆	Continuous Detector Current (Either Polarity)	±100	mA	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

INDIVIDUAL COMPONENT CHARACTERISTICS

Symbol	Paran	neter	Test Conditions	Min	Тур*	Max	Unit
EMITTER							
V _F	Input Forward Voltage		I _F = 16 mA	-	1.3	1.75	V
I _R	Reverse Leakage Curre	nt	V _R = 5 V	-	_	10	μΑ
СЈ	Capacitance	Capacitance		-	50	-	pF
OUTPUT DE	DUTPUT DETECTOR						
BV ₄₋₆	Breakdown Voltage Either Polarity	H11F1M, H11F2M	$I_{4-6} = 10 \mu A, I_F = 0$	30	_	-	V
		H11F3M		15	-	-	
I ₄₋₆	Off-State Dark Current		V ₄₋₆ = 15 V, I _F = 0	-	-	50	nA
			$V_{4-6} = 15 \text{ V, I}_F = 0,$ $T_A = 100^{\circ}\text{C}$	-	_	50	μΑ
R ₄₋₆	Off-State Resistance		V ₄₋₆ = 15 V, I _F = 0	300	_	-	МΩ
C ₄₋₆	Capacitance		$V_{4-6} = 15 \text{ V}, I_F = 0,$ f = 1 MHz	-	_	15	pF

TRANSFER CHARACTERISTICS

Symbol	Characte	ristics	Test Conditions	Min	Typ*	Max	Unit
C CHARA	CTERISTICS		•				
R ₄₋₆	On-State Resistance	H11F1M	$I_F = 16 \text{ mA}, I_{4-6} = 100 \mu\text{A}$	_	-	200	Ω
		H11F2M		_	-	330	
		H11F3M		-	-	470	
R ₆₋₄	On-State Resistance	H11F1M	$I_F = 16 \text{ mA}, I_{6-4} = 100 \mu\text{A}$	-	-	200	Ω
		H11F2M		-	-	330	
		H11F3M	7	-	-	470	
	Resistance, Non-Linearit	y and Assymetry	$I_F = 16 \text{ mA}, I_{4-6} = 25 \mu\text{A RMS}, f = 1 \text{ kHz}$	_	2	_	%
C CHARA	CTERISTICS		•				
t _{on}	Turn-On Time		$R_L = 50 \ \Omega, I_F = 16 \ mA, V_{4-6} = 5 \ V$	-	_	45	μs
t _{off}	Turn-Off Time		R_L = 50 Ω, I_F = 16 mA, V_{4-6} = 5 V	_	-	45	μs

ISOLATION CHARACTERISTICS

Symbol	Characteristics	Test Conditions	Min	Тур*	Max	Unit
V _{ISO}	Input-Output Isolation Voltage	t = 1 Minute	4170	-	-	VAC _{RMS}
R _{ISO}	Isolation Resistance	V _{I-O} = 500 VDC	10 ¹¹	-	-	Ω
C _{ISO}	Isolation Capacitance	f = 1 MHz	-	0.2	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. *All Typical values at T_A= 25°C.

TYPICAL PERFORMANCE CURVES

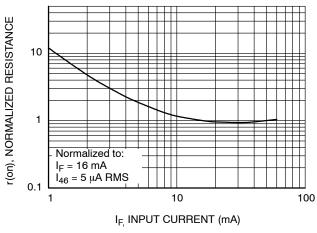


Figure 1. Resistance vs. Input Current

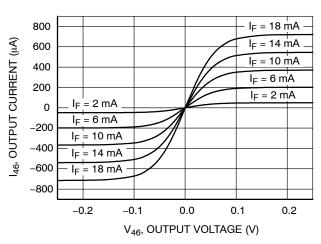


Figure 2. Output Characteristics

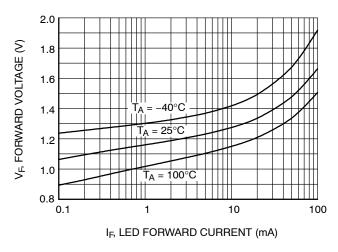


Figure 3. LED Forward Voltage vs. Forward Current

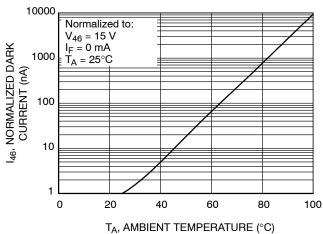


Figure 4. Off-State Current vs. Ambient Temperature

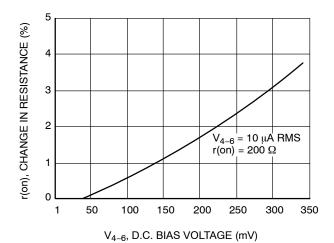
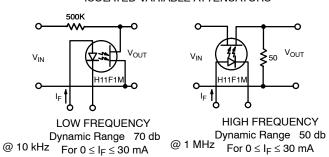


Figure 5. Resistive Non-Linearity vs. D.C. Bias

TYPICAL APPLICATIONS

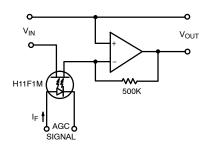
As a Variable Resistor

ISOLATED VARIABLE ATTENUATORS



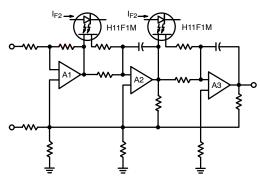
Distortion free attenuation of low level A.C. signals is accomplished by varying the IRED current, IF Note the wide dynamic range and absence of coupling capacitors; D.C. level shifting or parasitic feedback to the controlling function.

AUTOMATIC GAIN CONTROL



This simple circuit provides over 70db of stable gain control for an AGC signal range of from 0 to 30mA. This basic circuit can be used to provide programmable fade and attack for electronic music.

ACTIVE FILTER FINE TUNING/BAND SWITCHING

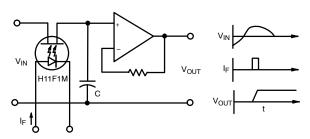


IF2 ADJUSTS f₁, IF2 ADJUSTS f₂

The linearity of resistance and the low offset voltage of the H11FXM allows the remote tuning or band-switching of active filters without switching glitches or distortion. This schematic illustrates the concept, with current to the H11F1M IRED 's controlling the filter's transfer characteristic.

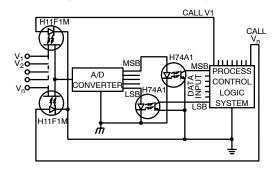
As an Analog Signal Switch

ISOLATED VARIABLE ATTENUATORS



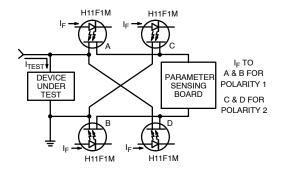
Accuracy and range are improved over conventional FET switches because the H11FXM has no charge injection from the control signal. The H11FXM also provides switching of either polarity input signal up to 30V magnitude.

MULTIPLEXED, OPTICALLY-ISSOLATED A/D CONVERSION



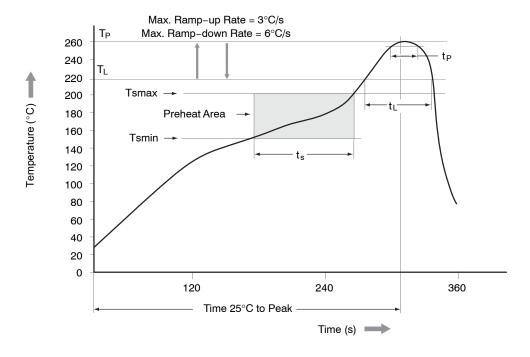
The optical isolation, linearity and low offset voltage of the H11FXM allows the remote multiplexing of low level analog signals from such transducers as thermocouplers, Hall effect devices, strain gauges, etc. to a single A/D converter.

TEST EQUIPMENT - KELVIN CONTACT POLARITY



In many test equipment designs the auto polarity function uses reed relay contacts to switch the Kelvin Contact polarity. These reeds are normally one of the highest maintenance cost items due to sticking contacts and mechanical problems. The totally solid–State H11FXM eliminates these troubles while providing faster switching.

REFLOW PROFILE



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/seconds max.
Liquidous Temperature (T _L)	217°C
Time (t $_{\rm L}$) Maintained Above (T $_{\rm L}$)	60-150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/seconds max.
Time 25°C to Peak Temperature	8 minutes max.

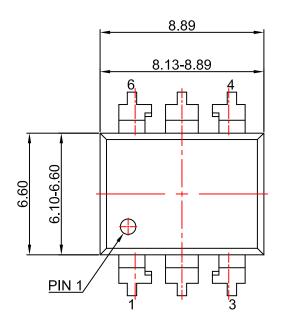
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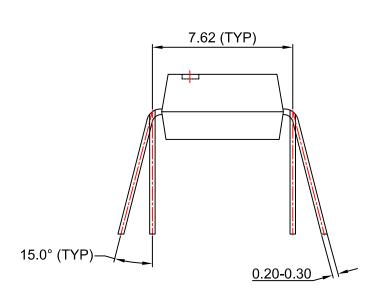
Option	Order Entry Identifier (Example)	Description
No option	H11F1M	Standard Through Hole Device
S	H11F1SM	Surface Mount Lead Bend
SR2	H11F1SR2M	Surface Mount; Tape and Reel
V	H11F1VM	IEC60747-5-5 approval
TV	H11F1TVM	IEC60747-5-5 approval, 0.4" Lead Spacing
SV	H11F1SVM	IEC60747-5-5 approval, Surface Mount
SR2V	H11F1SR2VM	IEC60747-5-5 approval, Surface Mount, Tape and Reel

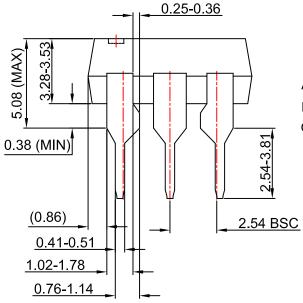


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DATE 31 JUL 2016







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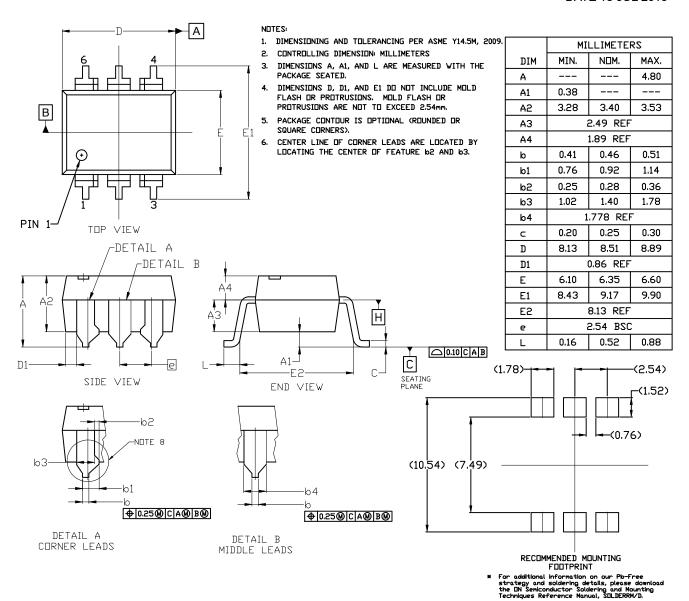
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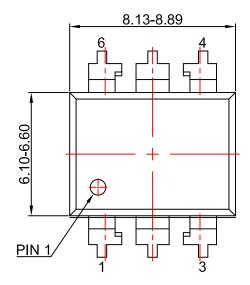


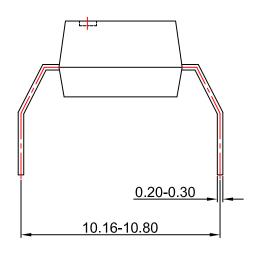
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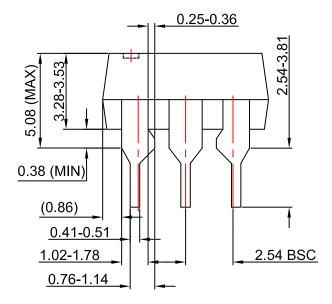
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